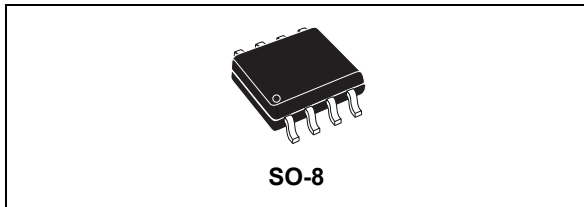


High voltage high- and low-side driver for automotive applications

Datasheet - production data



Features

- High voltage rail up to 550 V
- dV/dt immunity ± 50 V/nsec in full temperature range
- Driver current capability
 - 400 mA source
 - 650 mA sink
- Switching times 50/30 nsec rise/fall with 1 nF load
- CMOS/TTL Schmitt-trigger inputs with hysteresis and pull down
- Internal bootstrap diode

- Outputs in phase with inputs
- Interlocking function
- AECQ100 automotive qualified

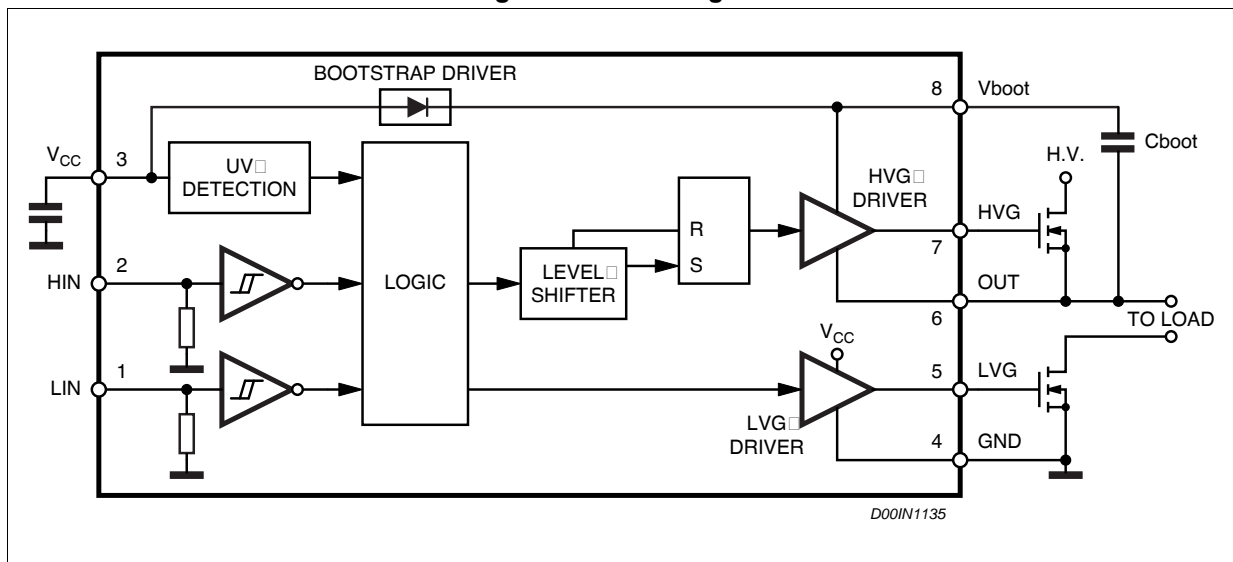
Applications

- Drive inverters for HEV and EV
- HID ballasts, power supply units
- Motion driver for home appliances, factory automation, industrial drives

Description

The A6387 is a high voltage device, manufactured with the BCD™ “offline” technology. It is a single chip half-bridge gate driver for N-channel Power MOSFETs or IGBTs. The high-side (floating) section is designed to stand a voltage rail of up to 550 V. The logic inputs are CMOS/TTL compatible for easy interfacing of the microcontroller or DSP.

Figure 1. Block diagram



Contents

- 1 Electrical data 3**
 - 1.1 Absolute maximum ratings 3
 - 1.2 Thermal data 3
 - 1.3 Recommended operating conditions 3

- 2 Pin connection 4**

- 3 Electrical characteristics 5**
 - 3.1 AC operation 5
 - 3.2 DC operation 6

- 4 Input logic 7**

- 5 Bootstrap driver 8**
 - C_{BOOT} selection and charging 8

- 6 Typical characteristic 10**

- 7 Package information 11**

- 8 Ordering information 13**

- 9 Revision history 13**

1 Electrical data

1.1 Absolute maximum ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Min.	Max.	Unit
V_{CC}	Supply voltage	- 0.3	18	V
V_{out}	Output voltage	$V_{boot} - 18$	$V_{boot} + 0.3$	V
V_{boot}	Bootstrap voltage	- 0.3	568	V
V_{hvg}	High-side gate output voltage	$V_{out} - 0.3$	$V_{boot} + 0.3$	V
V_{lvg}	Low-side gate output voltage	- 0.3	$V_{CC} + 0.3$	V
V_i	Logic input voltage	- 0.3	$V_{CC} + 0.3$	V
dV_{out}/dt	Allowed output slew rate		50	V/ns
P_{tot}	Total power dissipation ($T_A = 85\text{ °C}$)		750	mW
T_j	Junction temperature		150	°C
T_{stg}	Storage temperature	-50	150	°C
ESD	Human Body Model	2		kV

1.2 Thermal data

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{th(JA)}$	Thermal resistance junction to ambient	150	°C/W

1.3 Recommended operating conditions

Table 3. Recommended operating conditions

Symbol	Pin	Parameter	Test condition	Min.	Max.	Unit
V_{CC}	3	Supply voltage		6.3	17	V
$V_{BO}^{(1)}$	8 - 6	Floating supply voltage			17	V
V_{out}	7	Output voltage		-6 ⁽²⁾	530	V
f_{sw}		Switching frequency	HVG, LVG load $C_L = 1\text{ nF}$		400	kHz
T_j		Junction temperature		-40	125	°C

1. $V_{BO} = V_{boot} - V_{out}$.

2. LVG off. $V_{CC} = 12\text{ V}$.

2 Pin connection

Figure 2. Pin connection (top view)

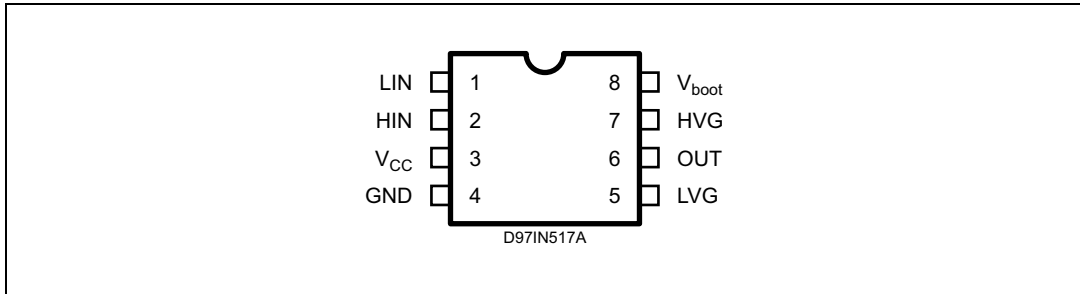


Table 4. Pin description

No.	Pin	Type	Function
1	LIN	I	Low-side driver logic input
2	HIN	I	High-side driver logic input
3	V _{CC}	P	Low voltage power supply
4	GND	P	Ground
5	LVG ⁽¹⁾	O	Low-side driver output
6	OUT	P	High-side driver floating reference
7	HVG ⁽¹⁾	O	High-side driver output
8	V _{boot}	P	Bootstrap supply voltage

1. The circuit provides less than 1 V on the LVG and HVG pins (at I_{sink} = 10 mA). This allows the omitting of the “bleeder” resistor connected between the gate and the source of the external MOSFET normally used to hold the pin low.

3 Electrical characteristics

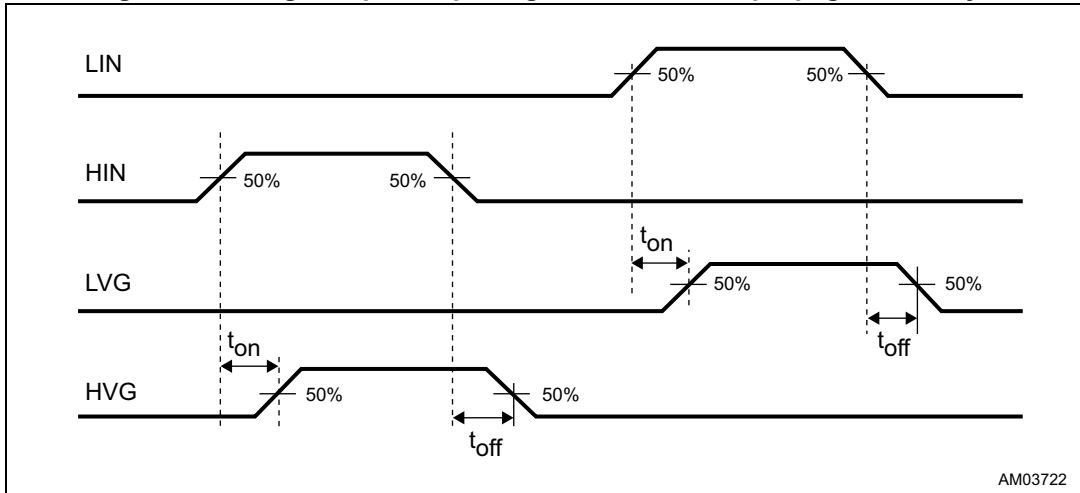
3.1 AC operation

$V_{CC} = 15\text{ V}$; $T_J = -40\text{ }^\circ\text{C} \div 125\text{ }^\circ\text{C}$, unless otherwise specified.

Table 5. AC operation electrical characteristics

Symbol	Pin	Parameter	Test condition	Min.	Typ.	Max.	Unit
t_{on}	1 vs. 5 2 vs. 7	High/low-side driver turn-on propagation delay	$V_{out} = 0\text{ V}$ $V_{boot} = V_{CC}$ $C_L = 1\text{ nF}$	40	120	240	ns
t_{off}	1 vs. 5 2 vs. 7	High/low-side driver turn-off propagation delay		40	110	210	ns
t_r	5, 7	Rise time	$C_L = 1\text{ nF}$		50	100	ns
t_f	5, 7	Fall time			30	80	ns

Figure 3. Timing of input/output signals; turn-on/off propagation delays



3.2 DC operation

V_{CC} = 15 V; T_J = -40 °C ÷ 125 °C, unless otherwise specified

Table 6. DC operation electrical characteristics

Symbol	Pin	Parameter	Test condition	Min.	Typ.	Max.	Unit
Low supply voltage section							
V _{CC_thON}	3	V _{CC} UV turn-on threshold		5.5	6	6.3	V
V _{CC_thOFF}		V _{CC} UV turn-off threshold		5	5.5	6	V
V _{CC_hys}		V _{CC} UV hysteresis		0.3	0.5	0.7	V
I _{qccu}		Undervoltage quiescent supply current	V _{CC} ≤ 5 V		150	220	μA
I _{qcc}		Quiescent current			250	320	μA
R _{DSon}		Bootstrap driver on resistance ⁽¹⁾	LVG ON		125		Ω
Bootstrapped supply voltage section ⁽²⁾							
I _{QBO}	8	V _{BO} quiescent current	HVG ON			100	μA
I _{LK}		High voltage leakage current	V _{hvg} = V _{out} = V _{boot} = 550 V			10	μA
High/low-side driver							
I _{so}	5, 7	High/low-side source short-circuit current	V _{IN} = V _{ih} (t _p < 10 μs)	300	400		mA
I _{si}		High/low-side sink short-circuit current	V _{IN} = V _{il} (t _p < 10 μs)	450	650		mA
Logic inputs							
V _{il}	1,2	Low level logic threshold voltage				1.4	V
V _{ih}		High level logic threshold voltage		3.2			V
I _{ih}		High level logic input current	V _{IN} = 15 V	8	20	40	μA
I _{il}		Low level logic input current	V _{IN} = 0 V			1	μA

1. R_{DS(on)} is tested in the following way:

$$R_{DS(on)} = \frac{(V_{CC} - V_{BOOT1}) - (V_{CC} - V_{BOOT2})}{I_1(V_{CC}, V_{BOOT1}) - I_2(V_{CC}, V_{BOOT2})}$$

where I₁ is pin 8 current when V_{BOOT} = V_{BOOT1}, I₂ when V_{BOOT} = V_{BOOT2}.

2. V_{BO} = V_{boot} - V_{out}.

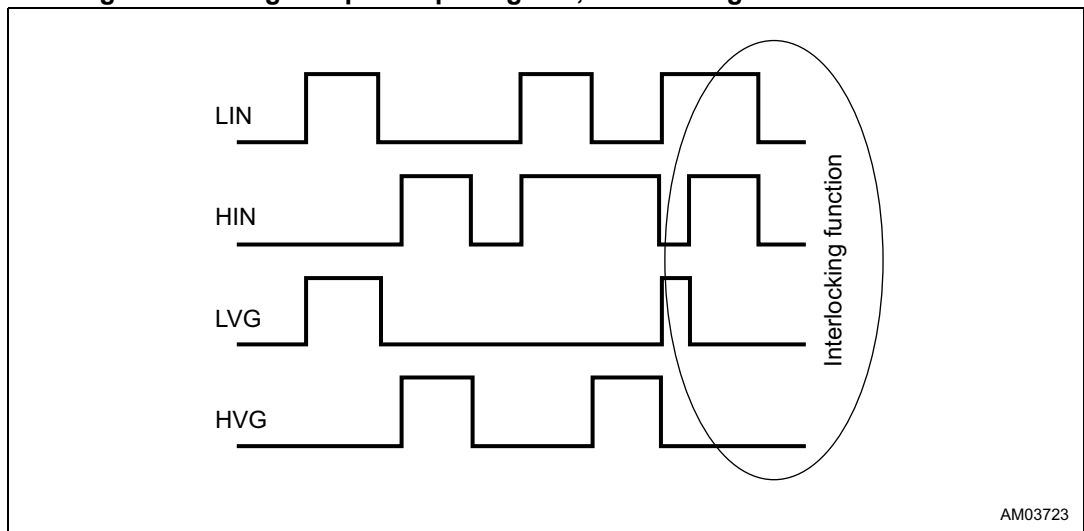
4 Input logic

The A6387 input logic is V_{CC} (17 V) compatible. An interlocking feature is offered (see [Table 7](#)) to avoid undesired simultaneous turn-on of both power switches driven.

Table 7. Input logic

Input		Output	
HIN	LIN	HVG	LVG
0	0	0	0
0	1	0	1
1	0	1	0
1	1	0	0

Figure 4. Timing of input/output signals; interlocking waveforms definition



5 Bootstrap driver

A bootstrap circuitry is needed to supply the high voltage section. This function is normally accomplished by a high voltage fast recovery diode (*Figure 5 a*). In the A6387 device a patented integrated structure replaces the external diode. It is realized by a high voltage DMOS, driven synchronously with the low-side driver (LVG), with a diode in series, as shown in *Figure 5 b*. An internal charge pump (*Figure 5 b*) provides the DMOS driving voltage.

C_{BOOT} selection and charging

To choose the proper C_{BOOT} value the external MOS can be seen as an equivalent capacitor. This capacitor C_{EXT} is related to the MOS total gate charge:

Equation 1

$$C_{EXT} = \frac{Q_{gate}}{V_{gate}}$$

The ratio between the capacitors C_{EXT} and C_{BOOT} is proportional to the cyclical voltage loss. It must be:

$$C_{BOOT} \gg C_{EXT}$$

For example: if Q_{gate} is 30 nC and V_{gate} is 10 V, C_{EXT} is 3 nF. With $C_{BOOT} = 100$ nF the drop would be 300 mV.

If HVG must be supplied for a long period, the C_{BOOT} selection must take into account also the leakage and quiescent losses.

For example: HVG steady-state consumption is lower than 100 μ A, therefore, if HVG T_{ON} is 5 ms, C_{BOOT} must supply 0.5 μ C to C_{EXT} . This charge on a 1 μ F capacitor means a voltage drop of 0.5 V.

The internal bootstrap driver offers a big advantage: the external fast recovery diode can be avoided (it usually has very high leakage current).

This structure can work only if V_{OUT} is close to GND (or lower) and, in the meantime, the LVG is on. The charging time (T_{charge}) of the C_{BOOT} is the time in which both conditions are fulfilled and it must be long enough to charge the capacitor.

The bootstrap driver introduces a voltage drop due to the DMOS R_{DSon} (typical value: 125 Ω). This drop can be neglected at low switching frequency, but it should be taken into account when operating at high switching frequency.

Equation 2 is useful to compute the drop on the bootstrap DMOS:

Equation 2

$$V_{drop} = I_{charge} R_{dson} \rightarrow V_{drop} = \frac{Q_{gate}}{T_{charge}} R_{dson}$$

where Q_{gate} is the gate charge of the external power MOS, R_{DSon} is the ON-resistance of the bootstrap DMOS, and T_{charge} is the charging time of the bootstrap capacitor.

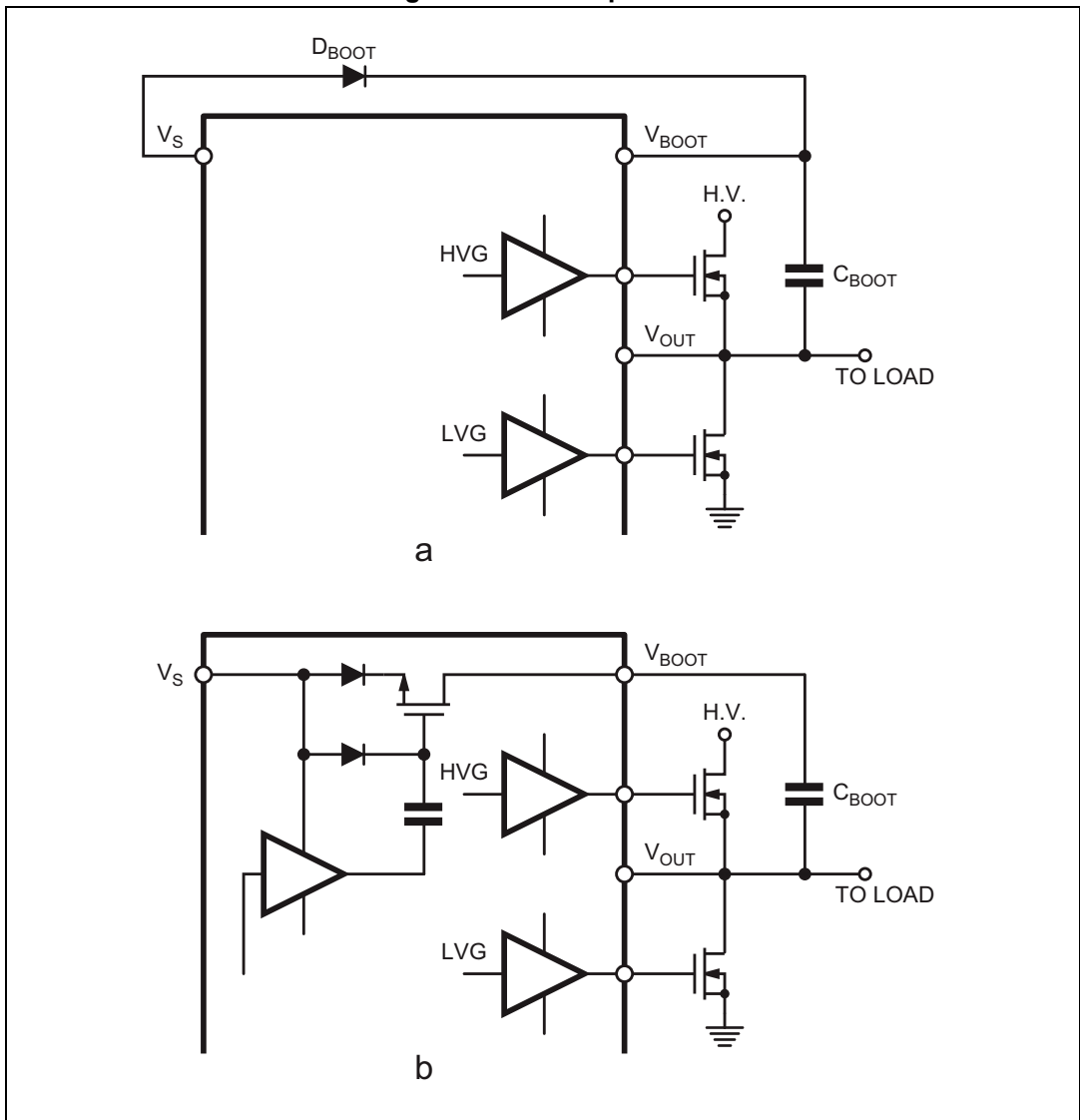
For example: using a power MOS with a total gate charge of 30 nC, the drop on the bootstrap DMOS is about 1 V, if the T_{charge} is 5 μs . In fact:

Equation 3

$$V_{drop} = \frac{30nC}{5\mu s} \cdot 125\Omega \sim 0.8V$$

V_{drop} should be taken into account when the voltage drop on C_{BOOT} is calculated: if this drop is too high, or the circuit topology doesn't allow a sufficient charging time, an external diode can be used.

Figure 5. Bootstrap driver



6 Typical characteristic

Figure 6. Typical rise and fall times vs. load capacitance

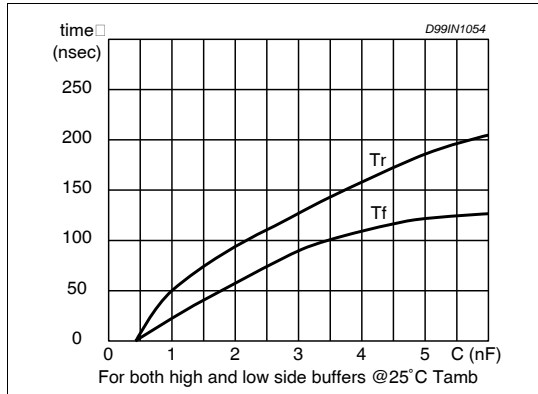


Figure 7. Quiescent current vs. supply voltage

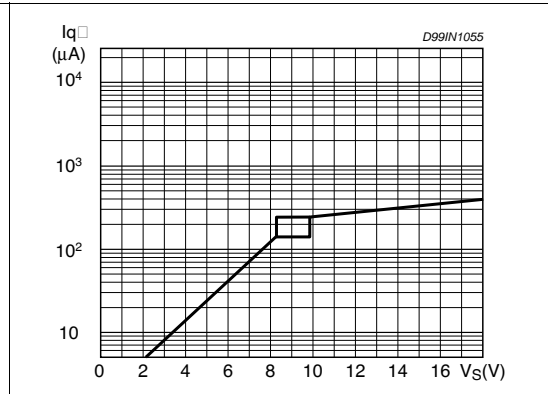


Figure 8. Turn-on time vs. temperature

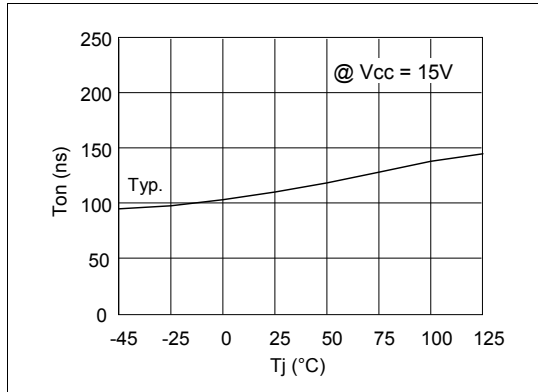


Figure 9. Turn-off time vs. temperature

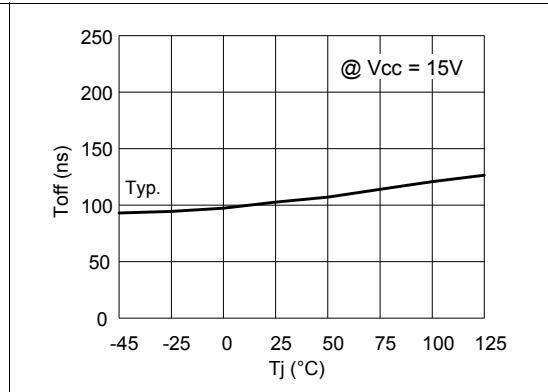


Figure 10. Output source current vs. temperature

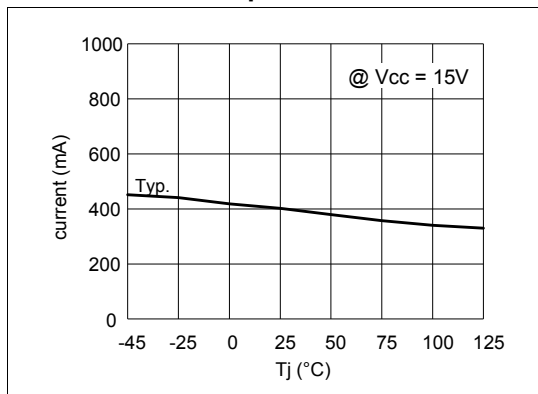
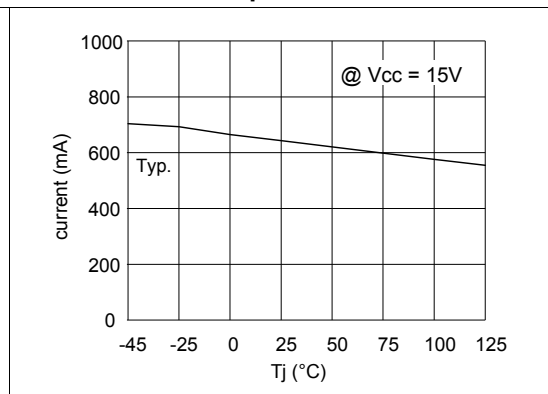


Figure 11. Output sink current vs. temperature



7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Figure 12. SO-8 package outline

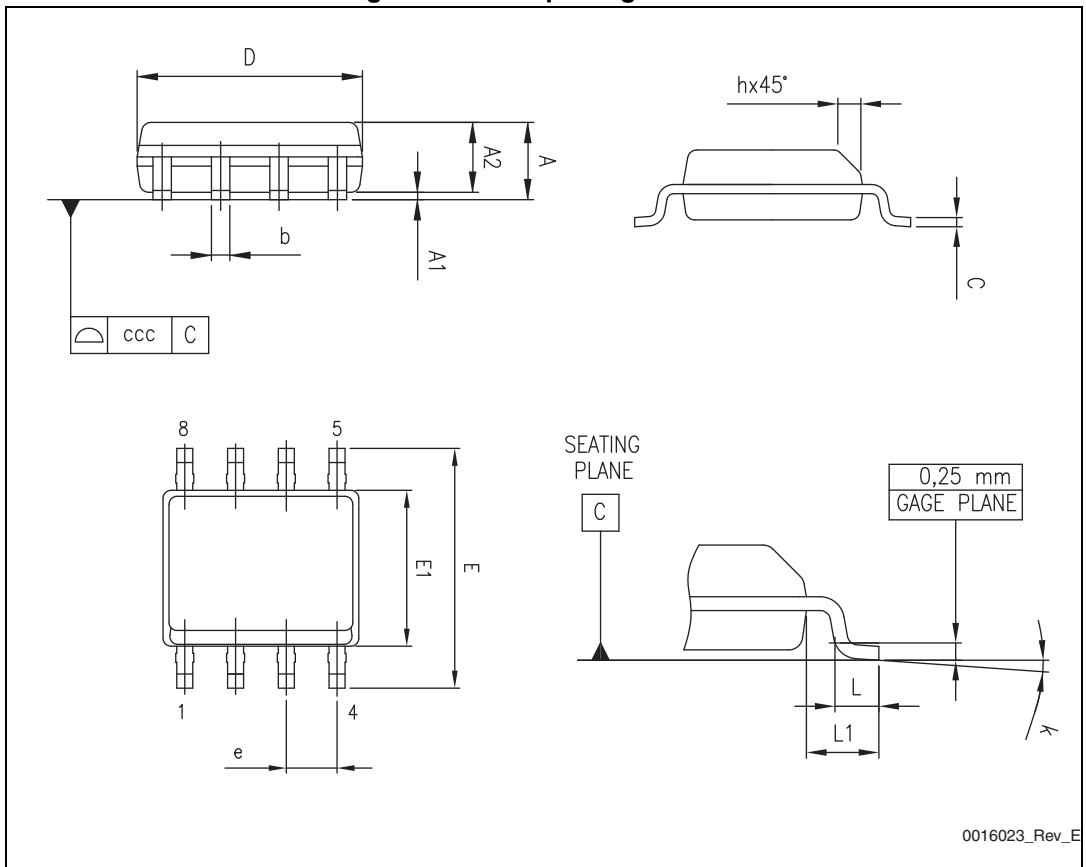


Table 8. SO-8 package mechanical data

Symbol	Dimensions (mm)		
	Min.	Typ.	Max.
A			1.75
A1	0.10		0.25
A2	1.25		
b	0.28		0.48
c	0.17		0.23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e		1.27	
h	0.25		0.50
L	0.40		1.27
L1		1.04	
k	0°		8°
ccc			0.10

8 Ordering information

Table 9. Ordering information

Order code	Package	Packaging
A6387D	SO-8	Tube
A6387DTR	SO-8	Tape and reel

9 Revision history

Table 10. Document revision history

Date	Revision	Changes
05-Jul-2012	1	First release
10-Oct-2013	2	Updated: Section : Features on page 1 (added "AECQ100 compliant"). Section : Applications on page 1 added: – Drive inverters for HEV and EV, – HID ballasts, power supply units, – Motion driver for home appliances, factory automation, industrial drives. Table 1 on page 3 (removed note below Table 1). Minor corrections throughout document.
22-Oct-2013	3	Updated Section : Features on page 1 ("replaced AECQ100 compliant" by "AECQ100 automotive qualified").
14-Apr-2014	4	Updated Section 3.1: AC operation on page 5 (added Figure 3). Updated Section 4: Input logic on page 7 (added Figure 4).
04-Feb-2015	5	Updated Table 1 (added <i>Human Body Model</i> parameter). Updated minimum supply voltage in Table 3 and maximum V_{CC} UV turn-on threshold voltage in Table 6 . Corrected typo in $R_{DS(on)}$ testing equation in footnote of Table 6 . Updated Figure 5: Bootstrap driver .

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